

Andrew I Yakimov

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

150
papers

1,731
citations

21
h-index

35
g-index

159
ext. papers

1,829
ext. citations

1.9
avg, IF

4.26
L-index

#	Paper	IF	Citations
150	Effect of Adhesive Layers on Photocurrent Enhancement in Near-Infrared Quantum-Dot Photodetectors Coupled with Metal-Nanodisk Arrays. <i>Semiconductors</i> , 2021 , 55, 654	0.7	
149	Increase in the Photocurrent in Layers of Ge/Si Quantum Dots by Modes of a Two-Dimensional Photonic Crystal. <i>JETP Letters</i> , 2021 , 113, 498-503	1.2	2
148	Near-Infrared Photoresponse in Ge/Si Quantum Dots Enhanced by Photon-Trapping Hole Arrays. <i>Nanomaterials</i> , 2021 , 11,	5.4	2
147	Near-infrared photoresponse in Ge/Si quantum dots enhanced by localized surface plasmons supported by aluminum nanodisks. <i>Journal of Applied Physics</i> , 2020 , 128, 143101	2.5	7
146	Quantum dot based mid-infrared photodetector enhanced by a hybrid metal-dielectric optical antenna. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 335105	3	9
145	Plasmon Enhancement of the Electric Field in Mid-Infrared Ge/Si Quantum-Dot Photodetectors with Different Thicknesses of the Active Region. <i>Semiconductors</i> , 2019 , 53, 195-199	0.7	
144	Plasmonic Field Enhancement by Metallic Subwave Lattices on Silicon in the Near-Infrared Range. <i>JETP Letters</i> , 2019 , 110, 411-416	1.2	2
143	Energy Spectrum of Charge Carriers in Elastically Strained Assemblies of Ge/Si Quantum Dots. <i>Journal of Surface Investigation</i> , 2018 , 12, 306-316	0.5	
142	Surface plasmon dispersion in a mid-infrared Ge/Si quantum dot photodetector coupled with a perforated gold metasurface. <i>Applied Physics Letters</i> , 2018 , 112, 171107	3.4	15
141	Comparison of two-dimensional arrays of gold disks and holes for plasmonic enhancement of Ge/Si quantum dot mid-infrared photodetectors. <i>Optical Materials Express</i> , 2018 , 8, 3479	2.6	8
140	Localization of Surface Plasmon Waves in Hybrid Photodetectors with Subwavelength Metallic Arrays. <i>JETP Letters</i> , 2018 , 108, 374-378	1.2	
139	Enhanced Optical Properties of Silicon Based Quantum Dot Heterostructures. <i>Defect and Diffusion Forum</i> , 2018 , 386, 68-74	0.7	2
138	Self-assembled strained GeSiSn nanoscale structures grown by MBE on Si(100). <i>Journal of Crystal Growth</i> , 2017 , 457, 215-219	1.6	3
137	Valence-band offsets in strained SiGeSn/Si layers with different tin contents. <i>Semiconductors</i> , 2017 , 51, 329-334	0.7	
136	Silicon-Based Nanoheterostructures With Quantum Dots 2017 , 59-99		6
135	Plasmon polariton enhanced mid-infrared photodetectors based on Ge quantum dots in Si. <i>Journal of Applied Physics</i> , 2017 , 122, 133101	2.5	17
134	Selective enhancement of the hole photocurrent by surface plasmon polaritons in layers of Ge/Si quantum dots. <i>JETP Letters</i> , 2017 , 105, 426-429	1.2	

133	Development of a high-voltage waveguide photodetector comprised of Schottky diodes and based on the GeSi structure with Ge quantum dots for portable thermophotovoltaic converters. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2017 , 53, 190-196	0.6	2
132	Simulation-Based Multi-Criterion Approach to Production Processes Control. <i>IFAC-PapersOnLine</i> , 2017 , 50, 15580-15585	0.7	0
131	Photovoltaic Ge/SiGe quantum dot mid-infrared photodetector enhanced by surface plasmons. <i>Optics Express</i> , 2017 , 25, 25602-25611	3.3	24
130	Photoconductive gain and quantum efficiency of remotely doped Ge/Si quantum dot photodetectors. <i>Materials Research Express</i> , 2016 , 3, 105032	1.7	14
129	Enhancement of the hole photocurrent in layers of Ge/Si quantum dots with abrupt heterointerfaces. <i>JETP Letters</i> , 2016 , 104, 479-482	1.2	
128	Phonon bottleneck in p-type Ge/Si quantum dots. <i>Applied Physics Letters</i> , 2015 , 107, 213502	3.4	14
127	Localization of electrons in dome-shaped GeSi/Si islands. <i>Applied Physics Letters</i> , 2015 , 106, 032104	3.4	12
126	Strain-induced localization of electrons in layers of the second-type Ge/Si quantum dots. <i>JETP Letters</i> , 2015 , 101, 750-753	1.2	7
125	Suppression of hole relaxation in small Ge/Si quantum dots. <i>JETP Letters</i> , 2015 , 102, 594-598	1.2	5
124	On the process of hole trapping in Ge/Si heterostructures with Ge quantum dots. <i>Semiconductors</i> , 2014 , 48, 1036-1040	0.7	4
123	Electronic states in vertically ordered Ge/Si quantum dots detected by photocurrent spectroscopy. <i>Physical Review B</i> , 2014 , 90,	3.3	14
122	Strain-dependent intersubband absorption in the valence band of SiGe quantum wells. <i>Semiconductor Science and Technology</i> , 2014 , 29, 045008	1.8	0
121	Influence of delta-doping on the hole capture probability in Ge/Si quantum dot mid-infrared photodetectors. <i>Nanoscale Research Letters</i> , 2014 , 9, 504	5	2
120	Hydrogen passivation of self-assembled Ge/Si quantum dots. <i>Semiconductor Science and Technology</i> , 2014 , 29, 085011	1.8	9
119	Bidirectional photocurrent of holes in layers of Ge/Si quantum dots. <i>JETP Letters</i> , 2014 , 100, 91-94	1.2	2
118	Intraband optical transitions of holes in strained SiGe quantum wells. <i>JETP Letters</i> , 2013 , 97, 159-162	1.2	2
117	Broadband Ge/SiGe quantum dot photodetector on pseudosubstrate. <i>Nanoscale Research Letters</i> , 2013 , 8, 217	5	11
116	Ge/Si heterostructures with Ge quantum dots for mid-infrared photodetectors. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2013 , 49, 467-475	0.6	6

115	Influence of delta-doping on the performance of Ge/Si quantum-dot mid-infrared photodetectors. <i>Journal of Applied Physics</i> , 2012 , 112, 034511	2.5	19
114	Electronic structure of double Ge quantum dots in Si. <i>JETP Letters</i> , 2012 , 96, 75-83	1.2	
113	Photovoltaic Ge/Si quantum dot detectors operating in the mid-wave atmospheric window (3 to 5 μ m). <i>Nanoscale Research Letters</i> , 2012 , 7, 494	5	8
112	Photoinduced and equilibrium optical absorption in Ge/Si quantum dots. <i>Semiconductors</i> , 2012 , 46, 1529-1533	1.3	3
111	Effect of overgrowth temperature on the mid-infrared response of Ge/Si(001) quantum dots. <i>Applied Physics Letters</i> , 2012 , 100, 053507	3.4	16
110	Antibonding ground state of holes in double vertically coupled Ge/Si quantum dots. <i>JETP Letters</i> , 2012 , 94, 744-747	1.2	5
109	Infrared absorption and admittance spectroscopy of Ge quantum dots on a strained SiGe layer. <i>Semiconductor Science and Technology</i> , 2011 , 26, 125002	1.8	5
108	Midinfrared photoresponse of Ge quantum dots on a strained Si _{0.65} Ge _{0.35} layer. <i>Semiconductor Science and Technology</i> , 2011 , 26, 085018	1.8	7
107	Electromodulated reflectance study of self-assembled Ge/Si quantum dots. <i>Nanoscale Research Letters</i> , 2011 , 6, 208	5	6
106	Double-occupancy probability and entanglement of two holes in double Ge/Si quantum dots. <i>JETP Letters</i> , 2010 , 92, 36-39	1.2	2
105	Calculating the energy spectrum and electronic structure of two holes in a pair of strained Ge/Si coupled quantum dots. <i>Physical Review B</i> , 2010 , 81,	3.3	20
104	Investigation of time characteristics of photodetectors based on Ge/Si nanoheterostructures. <i>Russian Physics Journal</i> , 2010 , 53, 504-507	0.7	
103	Bonding–antibonding ground-state transition in coupled Ge/Si quantum dots. <i>Semiconductor Science and Technology</i> , 2009 , 24, 095002	1.8	12
102	Excitons in Ge/Si double quantum dots. <i>JETP Letters</i> , 2009 , 90, 569-573	1.2	7
101	Hole states in vertically coupled double Ge/Si quantum dots. <i>Microelectronics Journal</i> , 2009 , 40, 785-787	1.8	1
100	Physics and technology of quantum dot semiconductor nanostructures for IR application. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2009 , 73, 66-69	0.4	
99	Light absorption related to hole transitions in quantum dots and impurity centers in quantum wells under external excitation. <i>Journal of Physics: Conference Series</i> , 2009 , 193, 012059	0.3	1
98	Enhanced oscillator strength of interband transitions in coupled GeSi quantum dots. <i>Applied Physics Letters</i> , 2008 , 93, 132105	3.4	14

97	Asymmetry of single-particle hole states in a strained Ge/Si double quantum dot. <i>Physical Review B</i> , 2008 , 78,	3.3	11
96	Molecular ground hole state of vertically coupled GeSi/Si self-assembled quantum dots. <i>Nanotechnology</i> , 2008 , 19, 055202	3.4	4
95	MBE growth of ultra small coherent Ge quantum dots in silicon for applications in nanoelectronics. <i>Journal of Physics and Chemistry of Solids</i> , 2008 , 69, 669-672	3.9	6
94	SiGe Nanodots in Electro-Optical SOI Devices. <i>NATO Science for Peace and Security Series B: Physics and Biophysics</i> , 2007 , 113-128	0.2	1
93	MBE growth of vertically ordered Ge quantum dots on Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 262-264		2
92	Localization of electrons in type-II Ge/Si quantum dots stacked in a multilayer structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 442-444		
91	Hole states in artificial molecules formed by vertically coupled Ge/Si quantum dots. <i>JETP Letters</i> , 2007 , 85, 429-433	1.2	5
90	Bonding state of a hole in Ge/Si double quantum dots. <i>JETP Letters</i> , 2007 , 86, 478-481	1.2	5
89	Determination of the composition and strains in $\text{Ge}_x\text{Si}_{1-x}$ -based nanostructures from Raman spectroscopy data with consideration of the contribution of the heterointerface. <i>Semiconductors</i> , 2007 , 41, 930-934	0.7	9
88	SPACE-CHARGE SPECTROSCOPY OF ELECTRONIC STATES IN Ge/Si QUANTUM DOTS WITH TYPE-II BAND ALIGNMENT. <i>International Journal of Nanoscience</i> , 2007 , 06, 353-356	0.6	
87	Hole states in GeBi quantum-dot molecules produced by strain-driven self-assembly. <i>Journal of Applied Physics</i> , 2007 , 102, 093714	2.5	16
86	Raman scattering diagnostics of as grown and pulsed laser modified Ge-Si nanostructures with quantum dots 2007 ,		1
85	Localization of electrons in multiple layers of self-assembled GeSiBi islands. <i>Applied Physics Letters</i> , 2006 , 89, 163126	3.4	6
84	Effect of the growth rate on the morphology and structural properties of hut-shaped Ge islands in Si(001). <i>Nanotechnology</i> , 2006 , 17, 4743-7	3.4	24
83	Electronic states in GeBi quantum dots with type-II band alignment initiated by space-charge spectroscopy. <i>Physical Review B</i> , 2006 , 73,	3.3	62
82	Hopping magnetoresistance in two-dimensional arrays of Ge/Si quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 296-299		3
81	Binding of electron states in multilayer strained Ge/Si heterostructures with type-II quantum dots. <i>JETP Letters</i> , 2006 , 83, 156-161	1.2	7
80	Photoconduction in tunnel-coupled Ge/Si quantum dot arrays. <i>Journal of Experimental and Theoretical Physics</i> , 2006 , 103, 269-277	1	10

79	Modification of quantum dots in Ge/Si nanostructures by pulsed laser irradiation. <i>Semiconductors</i> , 2006 , 40, 202-209	0.7	9
78	Germanium Self-Assembled Quantum Dots in Silicon for Nano- and Optoelectronics. <i>Journal of Nanoelectronics and Optoelectronics</i> , 2006 , 1, 119-175	1.3	21
77	Effect of pulsed laser action on hole-energy spectrum of GeSi self-assembled quantum dots. <i>Physical Review B</i> , 2005 , 72,	3.3	22
76	AC-hopping conductance of self-organized Ge/Si quantum dot arrays. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005 , 26, 450-454	3	4
75	Quantum Dots Microstructure and Energy Spectrum Peculiarities. <i>Physica Scripta</i> , 2005 , 439	2.6	2
74	Ge/Si photodiodes and phototransistors with embedded arrays of germanium quantum dots for fiber-optic communication lines. <i>Physics of the Solid State</i> , 2005 , 47, 34	0.8	10
73	Si-Ge-GaAs nanoheterostructures for photovoltaic cells. <i>Physics of the Solid State</i> , 2005 , 47, 63	0.8	4
72	Hopping conductivity and Coulomb correlations in 2D arrays of Ge/Si quantum dots. <i>Journal of Experimental and Theoretical Physics</i> , 2005 , 100, 722	1	14
71	Mechanisms of low-temperature high-frequency conductivity in systems with a dense array of Ge _{0.7} Si _{0.3} quantum dots in silicon. <i>Journal of Experimental and Theoretical Physics</i> , 2005 , 101, 1122-1129 ¹		
70	Hopping photoconductivity and its long-time relaxation in two-dimensional array of Ge/Si quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 3118-3121		1
69	Ge/Si quantum dots in external electric and magnetic fields. <i>Physics of the Solid State</i> , 2004 , 46, 56-59	0.8	4
68	Self-assembling of Ge quantum dots in the CaF ₂ /Ge/CaF ₂ /Si heteroepitaxial system and the development of tunnel-resonance diode on its basis. <i>Physics of the Solid State</i> , 2004 , 46, 89-91	0.8	1
67	Ge/Si waveguide photodiodes with built-in layers of Ge quantum dots for fiber-optic communication lines. <i>Semiconductors</i> , 2004 , 38, 1225-1229	0.7	12
66	The Meyer-Neldel rule in the processes of thermal emission and hole capture in Ge/Si quantum dots. <i>JETP Letters</i> , 2004 , 80, 321-325	1.2	8
65	Non-equilibrium transport in arrays of type-II Ge/Si quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004 , 1, 21-24		1
64	Two-dimensional phononless VRH conduction in arrays of Ge/Si quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004 , 1, 51-54		2
63	Ge dots on Si (111) and (100) surfaces with SiO ₂ coverage: Raman study. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 23, 320-323	3	3
62	Molecular epitaxy and the electronic properties of Ge/Si heterosystems with quantum dots. <i>Low Temperature Physics</i> , 2004 , 30, 877-884	0.7	2

61	STARK SPECTROSCOPY OF Ge/Si(001) SELF-ASSEMBLED QUANTUM DOTS. <i>International Journal of Nanoscience</i> , 2003 , 02, 505-510	0.6	
60	GERMANIUM SELF-ASSEMBLED QUANTUM DOTS IN SILICON FOR MID-INFRARED PHOTODETECTORS. <i>Selected Topics in Electornics and Systems</i> , 2003 , 281-297	0	2
59	Phononless hopping conduction in two-dimensional layers of quantum dots. <i>JETP Letters</i> , 2003 , 77, 376-380	25	
58	Many-electron Coulomb correlations in hopping transport along layers of quantum dots. <i>JETP Letters</i> , 2003 , 78, 241-245	1.2	2
57	Pulsed-laser modification of germanium nanoclusters in silicon. <i>Semiconductors</i> , 2003 , 37, 1315-1320	0.7	4
56	Ge/Si photodiodes with embedded arrays of Ge quantum dots for the near infrared (1.3-1.5 μm) region. <i>Semiconductors</i> , 2003 , 37, 1345-1349	0.7	28
55	Hopping photoconduction and its long-time kinetics in a heterosystem with Ge quantum dots in Si. <i>JETP Letters</i> , 2003 , 78, 587-591	1.2	2
54	Evidence for two-dimensional correlated hopping in arrays of Ge/Si quantum dots. <i>Physical Review B</i> , 2003 , 68,	3.3	14
53	Stark effect in type-II Ge/Si quantum dots. <i>Physical Review B</i> , 2003 , 67,	3.3	33
52	Optical Properties Of Arrays Of Ge/Si Quantum Dots In Electric Field 2003 , 307-314		
51	Many-particle effects in excitonic transitions in type-II Ge/Si quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002 , 13, 1026-1029	3	3
50	Barrier height and tunneling current in Schottky diodes with embedded layers of quantum dots. <i>JETP Letters</i> , 2002 , 75, 102-106	1.2	4
49	Ge/Si quantum-dot metaloxide semiconductor field-effect transistor. <i>Applied Physics Letters</i> , 2002 , 80, 4783-4785	3.4	12
48	Growth and characterization of CaF ₂ /Ge/CaF ₂ /Si(111) quantum dots for resonant tunneling diodes operating at room temperature. <i>Applied Physics Letters</i> , 2002 , 81, 499-501	3.4	11
47	GERMANIUM SELF-ASSEMBLED QUANTUM DOTS IN SILICON FOR MID-INFRARED PHOTODETECTORS. <i>International Journal of High Speed Electronics and Systems</i> , 2002 , 12, 873-889	0.5	3
46	Electronic structure of Ge/Si quantum dots. <i>Nanotechnology</i> , 2002 , 13, 75-80	3.4	59
45	Raman scattering study of Ge dot superlattices. <i>Applied Surface Science</i> , 2001 , 175-176, 629-635	6.7	13
44	Local structure of self-organized uniform Ge quantum dots on Si(001). <i>Solid State Ionics</i> , 2001 , 141-142, 135-139	3.3	1

43	Contribution of the electron-electron interaction to the optical properties of dense arrays of Ge/Si quantum dots. <i>Journal of Experimental and Theoretical Physics</i> , 2001 , 92, 500-513	1	3
42	Spatial separation of electrons in Ge/Si(001) heterostructures with quantum dots. <i>JETP Letters</i> , 2001 , 73, 529-531	1.2	14
41	Type-II Ge/Si quantum dots. <i>Semiconductors</i> , 2001 , 35, 1095-1105	0.7	21
40	Spatially indirect excitons in self-assembled Ge/Si quantum dots. <i>Nanotechnology</i> , 2001 , 12, 441-446	3.4	8
39	Quantum dot Ge/Si heterostructures. <i>Physics-Uspexhi</i> , 2001 , 44, 1304-1307	2.8	3
38	Interlevel Ge/Si quantum dot infrared photodetector. <i>Journal of Applied Physics</i> , 2001 , 89, 5676-5681	2.5	84
37	Interband absorption in charged Ge/Si type-II quantum dots. <i>Physical Review B</i> , 2001 , 63,	3.3	48
36	Mechanism of Two-Level Hopping Current Fluctuations in Mesoscopic a-Si Based Structures. <i>Physica Status Solidi (B): Basic Research</i> , 2000 , 218, 155-158	1.3	
35	Hopping Transport through an Ensemble of Ge Self-Assembled Quantum Dots. <i>Physica Status Solidi (B): Basic Research</i> , 2000 , 218, 99-105	1.3	10
34	Molecular beam epitaxy of silicon-germanium nanostructures. <i>Thin Solid Films</i> , 2000 , 367, 75-84	2.2	69
33	In situ RHEED control of self-organized Ge quantum dots. <i>Thin Solid Films</i> , 2000 , 380, 158-163	2.2	40
32	Interlevel optical transitions and many-body effects in a dense array of Ge/Si quantum dots. <i>Thin Solid Films</i> , 2000 , 380, 82-85	2.2	2
31	Negative interband photoconductivity in Ge/Si heterostructures with quantum dots of the second type. <i>JETP Letters</i> , 2000 , 72, 186-189	1.2	7
30	Silicon-germanium nanostructures with quantum dots: Formation mechanisms and electrical properties. <i>Semiconductors</i> , 2000 , 34, 1229-1247	0.7	92
29	Raman scattering of Ge dot superlattices. <i>European Physical Journal B</i> , 2000 , 16, 355-359	1.2	21
28	Evidence for a negative interband photoconductivity in arrays of Ge/Si type-II quantum dots. <i>Physical Review B</i> , 2000 , 62, R16283-R16286	3.3	14
27	Depolarization shift of the in-plane polarized interlevel resonance in a dense array of quantum dots. <i>Physical Review B</i> , 2000 , 62, 9939-9942	3.3	19
26	Long-range Coulomb interaction in arrays of self-assembled quantum dots. <i>Physical Review B</i> , 2000 , 61, 10868-10876	3.3	58

25	Excitons in charged Ge/Si type-II quantum dots. <i>Semiconductor Science and Technology</i> , 2000 , 15, 1125-1130	1.3	31
24	Oscillations of hopping conductance in an array of charge-tunable self-assembled quantum dots. <i>Journal of Physics Condensed Matter</i> , 1999 , 11, 9715-9722	1.8	8
23	Hopping conduction and field effect in Si modulation-doped structures with embedded Ge quantum dots. <i>Physical Review B</i> , 1999 , 59, 12598-12603	3.3	36
22	Anisotropic negative magnetoresistance in one-dimensional channels of porous silicon. <i>JETP Letters</i> , 1999 , 69, 202-206	1.2	1
21	Normal-incidence infrared photoconductivity in Si p-i-n diode with embedded Ge self-assembled quantum dots. <i>Applied Physics Letters</i> , 1999 , 75, 1413-1415	3.4	101
20	One-dimensional localization in porous a-Si _{1-x} Mn _x . <i>JETP Letters</i> , 1998 , 67, 284-288	1.2	3
19	Formation of zero-dimensional hole states during molecular-beam epitaxy of Ge on Si (100). <i>JETP Letters</i> , 1998 , 68, 135-141	1.2	11
18	Effect of Spin-Glass Ordering on Conduction in a-Si _{1-x} Mn _x near the Metal-Insulator Transition. <i>Physica Status Solidi (B): Basic Research</i> , 1998 , 205, 299-303	1.3	7
17	Formation of zero-dimensional hole states in Ge/Si heterostructures probed with capacitance spectroscopy. <i>Thin Solid Films</i> , 1998 , 336, 332-335	2.2	33
16	The Kondo effect in amorphous. <i>Journal of Physics Condensed Matter</i> , 1997 , 9, 499-506	1.8	3
15	The temperature-induced transition from 3d to 1d hopping conduction in porous amorphous. <i>Journal of Physics Condensed Matter</i> , 1997 , 9, 889-899	1.8	2
14	Suppression of the fractal conductivity channel and superlocalization effects in porous a-Si:H. <i>Journal of Experimental and Theoretical Physics</i> , 1997 , 85, 501-506	1	3
13	Metal-insulator transition in amorphous Si _{1-x} Mn _x obtained by ion implantation. <i>JETP Letters</i> , 1997 , 65, 354-358	1.2	5
12	Longitudinal conductivity of Ge/Si heterostructures with quantum dots. <i>JETP Letters</i> , 1996 , 63, 444-447	1.2	4
11	Photostimulated mesoscopic current fluctuations in a-Si based microstructures. <i>JETP Letters</i> , 1996 , 64, 724-728	1.2	
10	Current-voltage characteristics of porous amorphous Si _{1-x} Mn _x in the one-dimensional hopping regime. <i>Philosophical Magazine Letters</i> , 1996 , 73, 17-26	1	5
9	Low-dimensional hopping conduction in porous amorphous silicon. <i>Physica B: Condensed Matter</i> , 1995 , 205, 298-304	2.8	19
8	Magnetic correlations on the insulating side of the metal-insulator transition in amorphous Si _{1-x} Mn _x . <i>Physical Review B</i> , 1995 , 51, 16549-16552	3.3	20

7	Hopping conduction and resonant tunnelling in amorphous silicon microstructures. <i>Journal of Physics Condensed Matter</i> , 1994 , 6, 2583-2594	1.8	7
6	Inelastic resonant tunneling in amorphous silicon microstructures. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1994 , 194, 133-136	2.3	1
5	Conductance oscillations in Ge/Si heterostructures containing quantum dots. <i>Journal of Physics Condensed Matter</i> , 1994 , 6, 2573-2582	1.8	39
4	Spontaneous fluctuations of variable-range hopping current in amorphous silicon microstructures. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1993 , 179, 131-134	2.3	8
3	“Coulomb staircase” in a Si/Ge structure. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1992 , 65, 701-705		3 ¹
2	Electrical properties of ion-doped amorphous silicon. <i>Physica Status Solidi A</i> , 1989 , 113, 519-527		3
1	Wide coulomb gap in localized states of 3d-metals in amorphous silicon. <i>Journal of Non-Crystalline Solids</i> , 1987 , 90, 111-114	3.9	1